

AMENDMENTS TO THE CLAIMS

The listing of claims below replaces all prior versions of claims in the application.

1-5. (Canceled)

6. (Currently Amended) A manufacturing method of a semiconductor device, comprising:

a step of forming an electrically conductive material film on a base board;

a redistribution board forming step of forming a redistribution board on a base board the base board, wherein the redistribution board forming step includes the step of applying copper plating on the electrically conductive material film;

a base board separating step of separating the base board from the redistribution board;

a semiconductor element mounting step of mounting at least one semiconductor element on the redistribution board via electrode pads formed on a surface of the redistribution board.

7-20. (Canceled)

21. (Previously Presented) The manufacturing method of the semiconductor device as claimed in claim 6, wherein the step of forming the redistribution board includes the step of forming the redistribution board incorporating a passive element on the base board.

22. (Previously Presented) The manufacturing method of the semiconductor device as claimed in claim 6, further comprising a redistribution board mounting step of mounting the redistribution board on a package board via electrode pads formed on an other surface of the redistribution board.

23. (Previously Presented) The manufacturing method of the semiconductor device as claimed in claim 6, wherein the base board is made of a silicon wafer, a plurality of the redistribution boards are integrally formed on said silicon wafer, and the redistribution boards are individualized after the base board removing step.

24. (Previously Presented) The manufacturing method of the semiconductor device as claimed in claim 6, wherein:

the base board is made of a sapphire board including a thin organic film formed on a surface where the redistribution board is formed; and

the base board separating step includes a step irradiating a laser beam to the thin organic film via the sapphire board and vaporizing the thin organic film.

25. (Previously Presented) The manufacturing method of the semiconductor device as claimed in claim 6, wherein:

the base board is made of silicon; and

the base board separating step includes a step of removing the silicon by using etching.

26. (Previously Presented) The manufacturing method of the semiconductor device as claimed in claim 25, wherein the base board separating step includes the step of removing the silicon by using etching and grinding together.

27. (Previously Presented) The manufacturing method of the semiconductor device as claimed in claim 6, wherein:

the base board is made of copper or copper alloy; and

the base board separating step includes a step of etching the base board.